

IN THE CLAIMS:

1.-45. (Cancelled)

46. (New) A semiconductor light emitting device having a luminous layer, comprising:

a light transmission layer disposed over a main surface of the luminous layer, and

5 having depressions on a surface facing away from the luminous layer; and

a transmission membrane disposed on the light transmission layer so as to follow contours of the depressions, wherein

light from the luminous layer is irradiated so as to pass through the light transmission layer and the transmission membrane, wherein the transmission membrane contains

10 a luminous substance that is excitable by the light from the luminous layer, the luminous layer is sandwiched between a plurality of layers and is disposed over the light transmission layer,

wherein the light transmission layer is made of a material having a refractive index that is substantially equal to a refractive index of the luminous layer and the material for the light transmission layer is selected from a group of GaN, SiC, and AlN.

47. (New) A semiconductor light emitting device having a luminous layer, comprising:

a light transmission layer disposed over a main surface of the luminous layer, and having depressions on a surface facing away from the luminous layer; and

5 a transmission membrane disposed on the light transmission layer so as to follow contours of the depressions, wherein

light from the luminous layer is irradiated so as to pass through the light transmission layer and the transmission membrane,

the luminous layer is sandwiched between a plurality of layers and is disposed
10 over the light transmission layer, wherein a refractive index that is substantially equal to a refractive index of the luminous layer, wherein a reflective film is disposed on a surface of the luminous layer facing away from the light transmission layer.

48. (New) A semiconductor light emitting device having a luminous layer, comprising:

a light transmission layer disposed over a main surface of the luminous layer, and having depressions on a surface facing away from the luminous layer; and

5 a transmission membrane disposed on the light transmission layer so as to follow contours of the depressions, wherein

light from the luminous layer is irradiated so as to pass through the light transmission layer and the transmission membrane, wherein the transmission membrane contains a luminous substance that is excitable by the light from the luminous layer, the luminous layer is
10 sandwiched between a plurality of layers and is disposed over the light transmission layer, wherein a reflective film is disposed on a surface of the luminous layer facing away from the light transmission layer.

49. (New) A semiconductor light emitting device having a luminous layer, comprising:

a light transmission layer disposed over a main surface of the luminous layer, and having depressions on a surface facing away from the luminous layer; and

5 a transmission membrane disposed on the light transmission layer so as to follow contours of the depressions, wherein

light from the luminous layer is irradiated so as to pass through the light transmission layer and the transmission membrane, and

the luminous layer is sandwiched between a plurality of layers and is disposed
10 over the light transmission layer, wherein light transmission layer is made of a material selected from a group of GaN, SiC, and AlN having a refractive index that is substantially equal to a refractive index of the luminous layer.